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(54) Title: METHOD OF MANUFACTURE OF CHALCOGENIDE-BASED PHOTOVOLTAIC CELLS

(57) Abstract: The invention is a method of forming a cadmium sulfide based buffer on a copper chalcogenide based absorber in making a photovoltaic cell. The buffer is sputtered at relatively high pressures. The resulting cell has good efficiency and according to one embodiment is characterized by a narrow interface between the absorber and buffer layers. The buffer is further characterized according to a second embodiment by a relatively high oxygen content.



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